P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)			
- 60	0.0208 at V _{GS} = - 10 V	- 66	76 nC			
- 60	0.0263 at V _{GS} = - 4.5 V	- 52	70110			

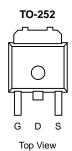
FEATURES

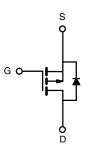
- DT-Trench Power MOSFET
- 100 % UIS Tested



APPLICATIONS

Load Switch





P-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	- 60	٧		
Gate-Source Voltage		V _{GS}	± 20		
	T _C = 25 °C		- 66 ^a		
Continuous Drain Current (T. – 150 °C)	T _C = 70 °C		- 46.8		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	l _D –	9.2 ^b		
	T _A = 70 °C		- 8.1 ^b	A	
Pulsed Drain Current		I _{DM}	- 180		
Avalanche Current Pulse	L = 0.1 mH	I _{AS}	- 35	1	
Single Pulse Avalanche Energy	L = 0.1 IIII1	E _{AS}	101	mJ	
Continuous Source-Drain Diode Current	T _C = 25 °C	I.	29 ^a	А	
Continuous Source-Diam Diode Current	T _A = 25 °C	l _S –	2.1 ^b		
	T _C = 25 °C		104.2 ^a		
Maninessa Dessa Dissipation	T _C = 70 °C		66.7 ^a	\\	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.1 ^b	W	
	T _A = 70 °C		2 ^b		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^b	Steady State	R _{thJA}	33	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.98	1.2]	

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		68		m\//°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		- 5.2		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	<u>μ</u> Α	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 120			Α	
Drain-Source On-State Resistance ^a	В	V _{GS} = - 10 V, I _D = - 30 A		0.0208	0.0231	Ω	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 20 A		0.0263	0.0298		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 50 A	20			S	
Dynamic ^b							
Input Capacitance	C _{iss}			3500		pF	
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		390			
Reverse Transfer Capacitance	C _{rss}			290			
Total Cata Chausa	Q _g	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -55 \text{ A}$		76	115		
Total Gate Charge				38	60		
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -55 \text{ A}$		16		110	
Gate-Drain Charge	Q_{gd}			19			
Gate Resistance	R_g	f = 1 MHz		5.2		Ω	
Turn-On Delay Time	t _{d(on)}			10	15		
Rise Time	t _r	V_{DD} = - 2 V, R_L = 2 Ω		7	15	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 10 A, $V_{GEN} =$ - 10 V, $R_g = 1 \Omega$		70	110		
Fall Time	t _f			40	60		
Drain-Source Body Diode Characteristic	S						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 66	A	
Pulse Diode Forward Current ^a	I _{SM}				- 180		
Body Diode Voltage	V_{SD}	I _S = - 30 A		- 1	- 1.5	V	
Body Diode Reverse Recovery Time	t _{rr}			45	68	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 50 A, di/dt = 100 A/μs, T _{.I} = 25 °C		59	120	nC	
Reverse Recovery Fall Time	t _a	$_{1F} = -30 \text{ A}, \text{ al/at} = 100 \text{ A/}\mu\text{s}, \text{ I}_{J} = 25 \text{ C}$		29		ns	
Reverse Recovery Rise Time	t _b			16			

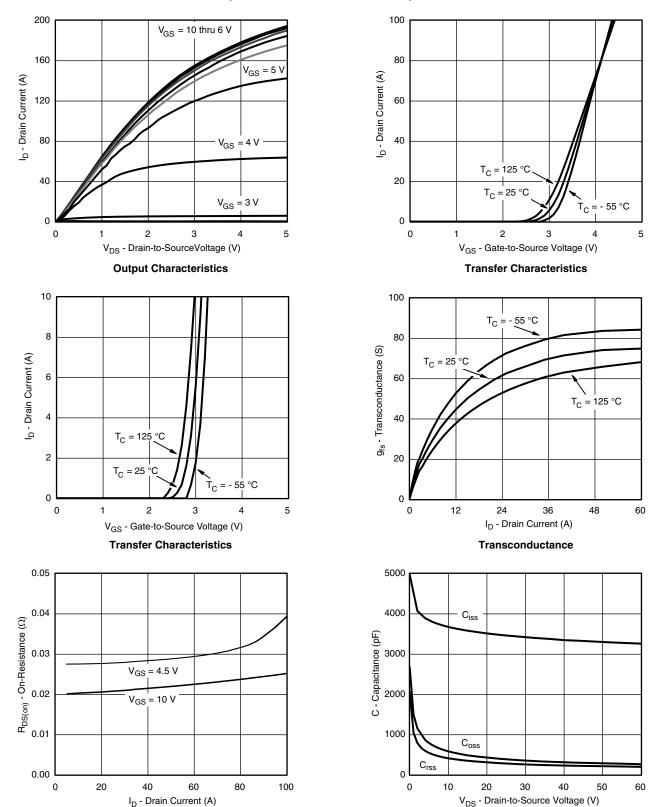
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

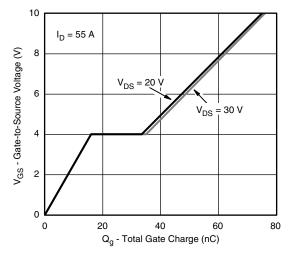
On-Resistance vs. Drain Current



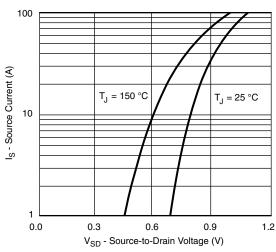
Capacitance



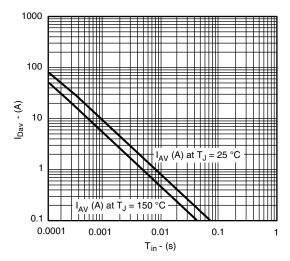
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



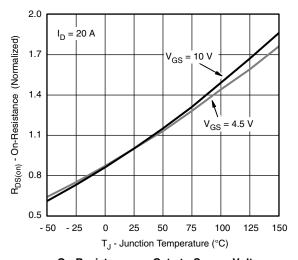
Gate Charge



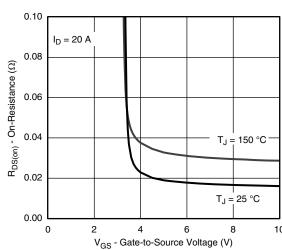
Source-Drain Diode Forward Voltage



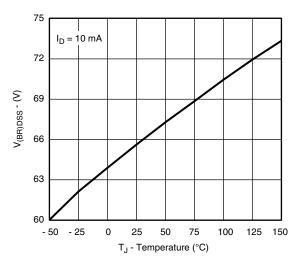
Single Pulse Avalanche Current Capability vs. Time



On-Resistance vs. Gate-to-Source Voltage

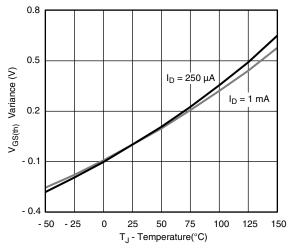


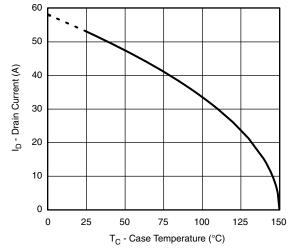
On-Resistance vs. Gate-to-Source Voltage



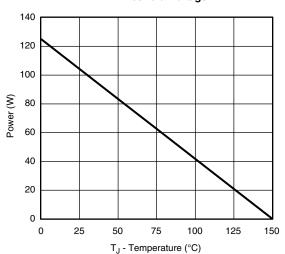
Drain-Source Breakdown Voltage vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

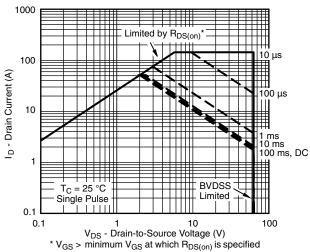




Threshold Voltage

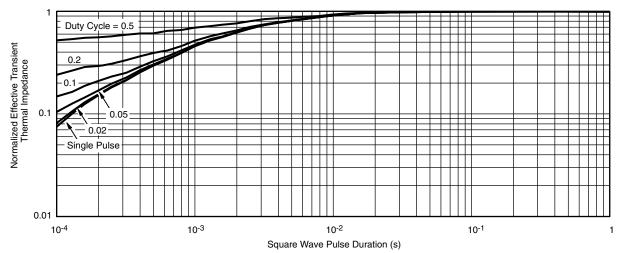


Max. Drain Current vs. Case Temperature



Power Derating, Junction-to-Case





Normalized Thermal Transient Impedance, Junction-to-Case

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